

N-Channel Enhancement Mode MOSFET

TO-92

SGD

High Speed Switching Application

Features

- ESD rating: 1000V (HBM)
- Low On-Resistance: $R_{DS(on)} < 3\Omega @ V_{GS} = 10V$
- High power and current handling capability
- · Very fast switching
- Halogen free and RoHS compliant device

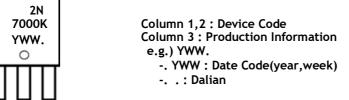
Applications

• High speed line driver

Ordering Information

Part Number	Marking Code	Package	Packaging		
KCK2N7000K	2N 7000K YWW.	TO-92	Таре		

Marking Information



Absolute Maximum Ratings (T_{amb}=25°C, Unless otherwise specified)

Characteristic	Symbol	Ratings	Unit
Drain-Source voltage	V _{DS}	60	V
Gate-Source voltage	V _{GS}	±20	V
Maximum drain current ^(Note 1)	Ι _D	500	mA
Pulsed drain current (Note 1)	I _{DP}	2	А
Power dissipation (Note 2)	P _D	625	mW
Operating junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	-55 ~ 150	°C
Thermal resistance junction to ambient (Note 2)	R _{th(j-a)}	400	°C/W

Note 1) Limited only maximum junction temperature

Note 2) Device mounted on FR-4 board with recommended pad layout.

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit	
Drian-Source breakdown voltage	BV _{DSS}	I _D =250μA, V _{GS} =0	60	-	-	V	
Gate-Source breakdown voltage	BV _{GSS}	I _G =250μA, V _{DS} =0	±20	-	-	V	
Gate-Threshold voltage	V _{GS(th)}	I_D =250uA, V_{DS} = V_{GS}	1	-	2.5	V	
Zero Gate voltage drain current	I _{DSS}	V _{DS} =60V, V _{GS} =0	-	-	1	μA	
Gate-body leakage	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±10	μA	
Note 3)		V _{GS} =10V, I _D =0.5A	-	-	3		
Drain-Source on-resistance ^(Note 3)	R _{DS(ON)}	V _{GS} =5V, I _D =0.05A	-	-	3.5	Ω	
Forward trans-conductance (Note 3)	g _{fs}	V _{DS} =10V, I _D =0.2A	0.08	-	-	S	
Input capacitance	C _{iss}	- 30		50			
Output capacitance	C _{oss}	V _{DS} =25V, V _{GS} =0, f=1MHz	-	7	-	pF	
Reverse Transfer capacitance	C _{rss}		-	4	-		
Turn-on delay time (Note 3, 4)	t _{d(on)}		-	2	-		
Rise time (Note 3, 4)	t _r	V _{DD} =30V, I _D =0.2A,	-	15	-	- ns	
Turn-off delay time (Note 3, 4)	t _{d(off)}	V_{GS} =10V, R_{G} =10 Ω		8	-		
Fall time (Note 3, 4)	t _f		-	11	-		
Total gate charge (Note 3, 4)	Qg		-	0.6	0.8		
Gate-Source charge (Note 3, 4)	Q _{gs}	V _{DS} =10V, I _D =0.25A, V _{GS} =4.5V	-	0.2	-	nC	
Gate-Drain charge (Note 3, 4)	Q _{gd}		-	0.2	-		
Diode forward voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =0.2A	-	-	1.3	V	

Electrical Characteristics (T_{amb}=25°C, Unless otherwise specified)

 $^{Note \; 3)}$ Pulse test: Pulse width ${\leq}300 us, \, Duty \; cycle {\leq} 2\%$

Note 4) Essentially independent of operating temperature typical characteristics.

Electrical Characteristics Curves

X Note :

1

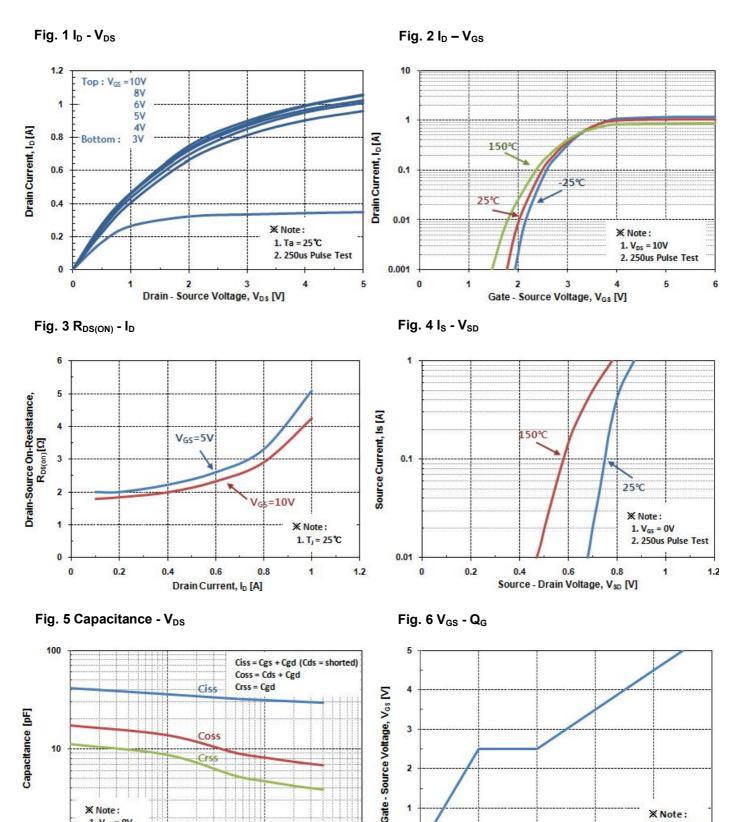
0.1

1. V_{GS} = 0V

2. f = 1MHz

1

Drain - Source Voltage, VDs [V]



100

10

1

0

0

0.2

0.4

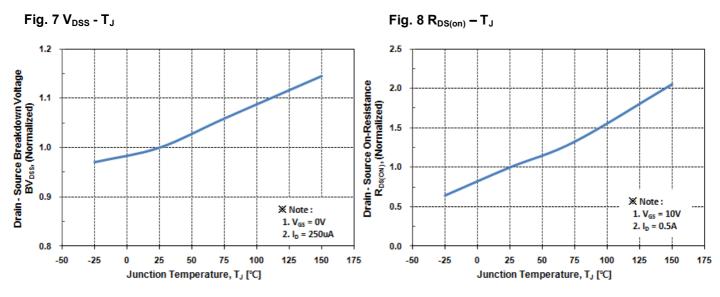
Drain - Source Voltage, VDs [V]

0.6

X Note:

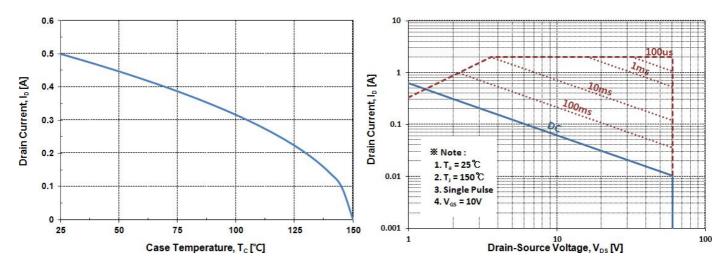
0.8

1. ID = 0.25A

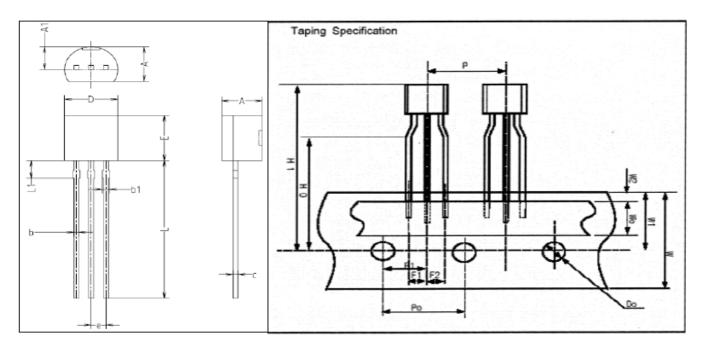








Package Outline Dimensions



Package Dimension(Unit : mm)			Taping Dimension(Unit : mm)				
Symbol	Min	Тур	Max	Symbol	Min	Тур	Max
A	3.40	3.56	3.66	P	12.2	12.7	13.2
A1	2.46	2.54	2.59	P0	12.5	12.7	12.9
b	0.39	0.48	0.53	P1	5.85	6.35	6.85
b1	0.39	-	0.63	F1,F2	2.4	2.5	2.9
с	0.35	0.42	0.47	W	17.5	18.0	19.0
D	4.48	4.60	4.70	W0	5.5	6.0	6.5
E	4.48	4.60	4.70	W1	8.5	9.0	9.5
e	1.17	1.27	1.37	W2	-1	-1	1.0
L	<u>13.70</u>	14.47	14.77	HO	15.5	<mark>16.</mark> 0	16.5
L1	1.55	1.70	2.15	H1	5	-	27.0
				D0	3.8	4.0	4.2

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